## NSN 5962-01-349-2196

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Storage Tempurature Range:
-65.0/+150.0 degrees celsius
Features Provided:
Hermetically sealed and monolithic and programmable and radiation hardened
Inclosure Material:
Ceramic
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Transistor-transistor logic
Input Circuit Pattern:
14 input
Criticality Code Justification:
Feat
Current Rating Per Characteristic:
100.00 milliamperes reverse current, dc absolute
Terminal Surface Treatment:
Solder
Product Name:
And gate array
Voltage Rating And Type Per Characteristic:
-0.5 volts power source and 7.0 volts power source
Time Rating Per Chacteristic:
40.00 nanoseconds propagation delay
Memory Device Type:
Pal
Special Features:
Nuclear hardness critical item
Test Data Document:
96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).
Terminal Type And Quantity:
24 printed circuit
Shelf Life:
N/a
Unit Of Measure:
Demilitarization:
Yes - demil/mli
Fiig:
A458a0